

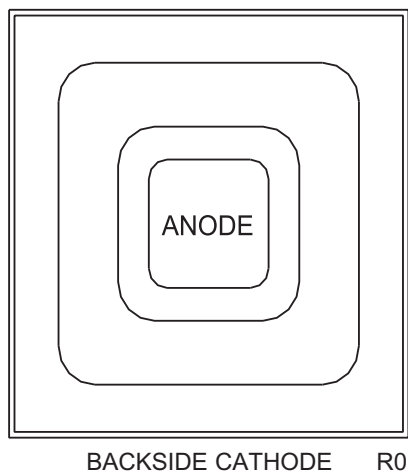
PROCESS CPD83V
Switching Diode
High Speed Switching Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	3.35 x 3.35 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER
137,880

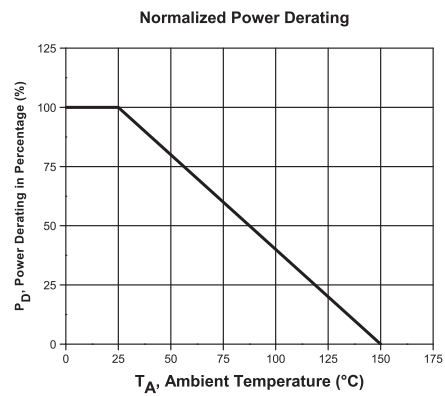
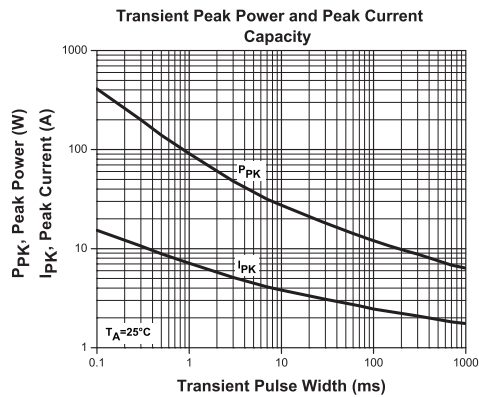
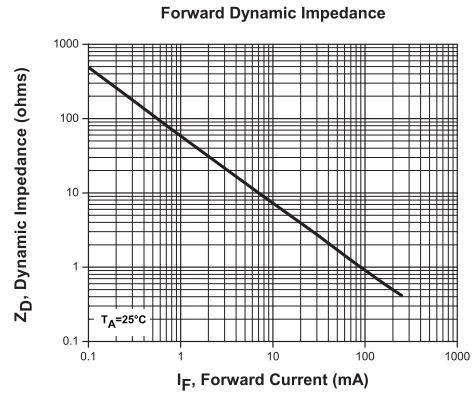
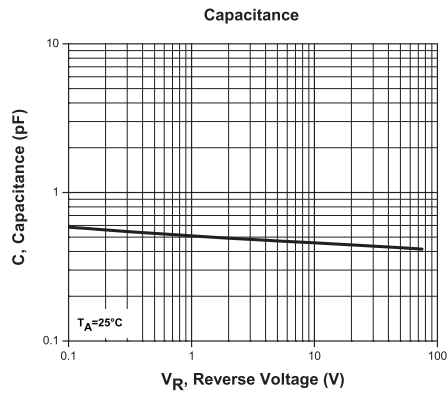
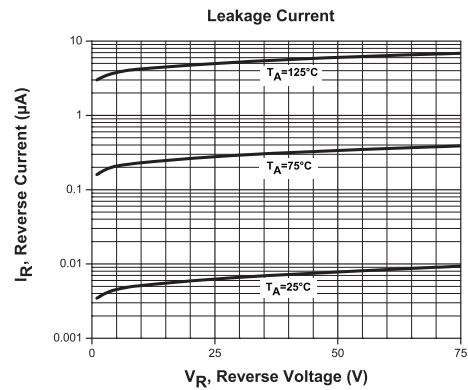
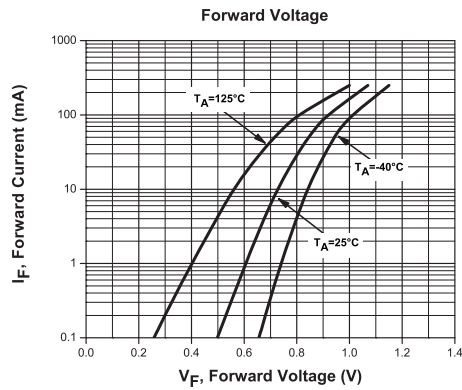
PRINCIPAL DEVICE TYPES

CMPD914
CMPD4448
1N914
1N914B
1N4148
1N4448
1N4154
1N4454
CMPD2836
CMPD2838
CMPD7000

R5 (22-March 2010)

PROCESS CPD83V

Typical Electrical Characteristics



R5 (22-March 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centalsemi.com

Worldwide Field Representatives:
www.centalsemi.com/wwreps

Worldwide Distributors:
www.centalsemi.com/wwdistributors

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